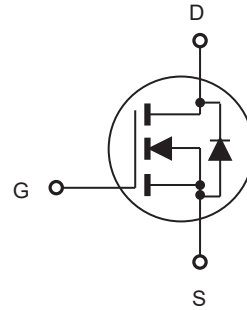
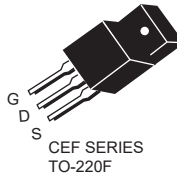


## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

Type	$V_{DS}@T_{Jmax}$	$R_{DS(ON)}$	$I_D$	@ $V_{GS}$
CEP07N8	850V	1.8Ω	7A	10V
CEB07N8	850V	1.8Ω	7A	10V
CEF07N8	850V	1.8Ω	7A <sup>d</sup>	10V

- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- RoHS compliant.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	$V_{DS}$	800		V
Gate-Source Voltage	$V_{GS}$	±30		V
Drain Current-Continuous @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_D$	7	7 <sup>d</sup>	A
		4.2	4.2 <sup>d</sup>	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}^e$	28	28 <sup>d</sup>	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above $25^\circ\text{C}$	$P_D$	205	52	W
		1.64	0.41	W/ $^\circ\text{C}$
Single Pulsed Avalanche Energy <sup>g</sup>	$E_{AS}$	125		mJ
Single Pulsed Avalanche Current <sup>g</sup>	$I_{AS}$	5		A
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.61	2.4	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	65	$^\circ\text{C}/\text{W}$



# CEP07N8/CEB07N8 CEF07N8

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 800V, V_{GS} = 0V$			1	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
<b>On Characteristics<sup>b</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	3		5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3.5A$		1.38	1.8	$\Omega$
<b>Dynamic Characteristics<sup>c</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		1030		pF
Output Capacitance	$C_{oss}$			105		pF
Reverse Transfer Capacitance	$C_{rss}$			20		pF
<b>Switching Characteristics<sup>c</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 7A,$ $V_{GS} = 10V, R_{GEN} = 10\Omega$		32		ns
Turn-On Rise Time	$t_r$			13		ns
Turn-Off Delay Time	$t_{d(off)}$			44		ns
Turn-Off Fall Time	$t_f$			12		ns
Total Gate Charge	$Q_g$	$V_{DS} = 640V, I_D = 7A,$ $V_{GS} = 10V$		25		nC
Gate-Source Charge	$Q_{gs}$			7		nC
Gate-Drain Charge	$Q_{gd}$			10		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Current	$I_S^f$				7	A
Drain-Source Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 7A$			1.4	V
<b>Notes :</b> a.Repetitive Rating : Pulse width limited by maximum junction temperature . b.Pulse Test : Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$ . c.Guaranteed by design, not subject to production testing. d.Limited only by maximum temperature allowed . e.Pulse width limited by safe operating area . f.Full package $I_{S(max)} = 3.4A$ . g.L = 10mH, $I_{AS} = 5A, V_{DD} = 50V, R_G = 25\Omega$ , Starting $T_J = 25^\circ\text{C}$ .						

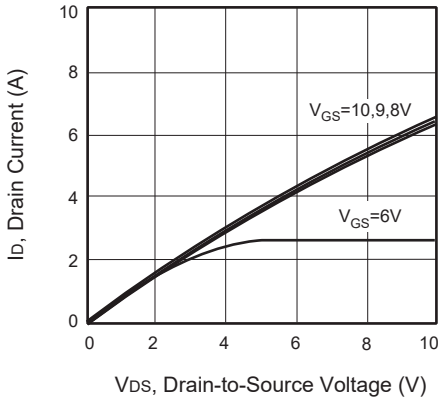


Figure 1. Output Characteristics

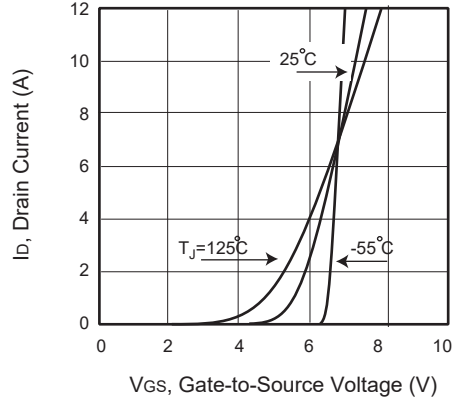


Figure 2. Transfer Characteristics

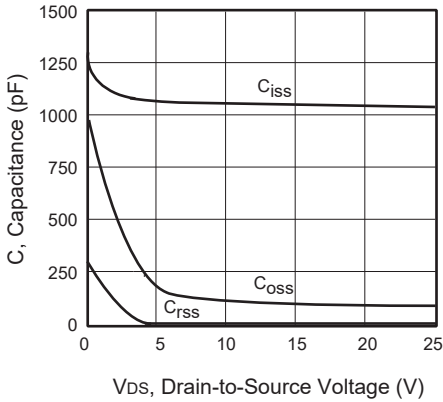


Figure 3. Capacitance

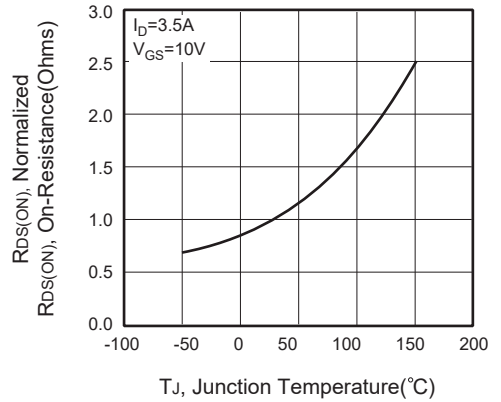


Figure 4. On-Resistance Variation with Temperature

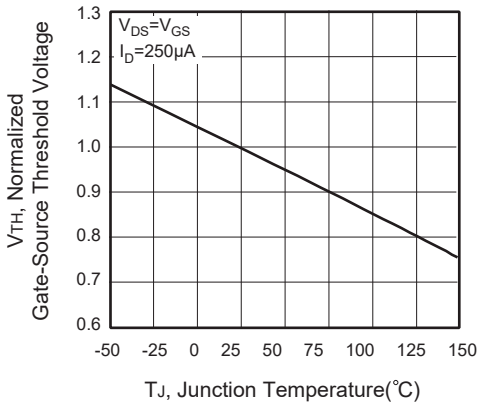


Figure 5. Gate Threshold Variation with Temperature

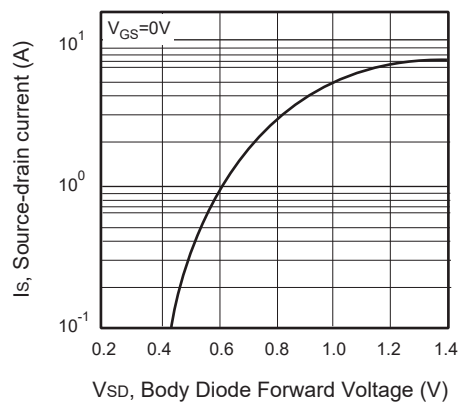
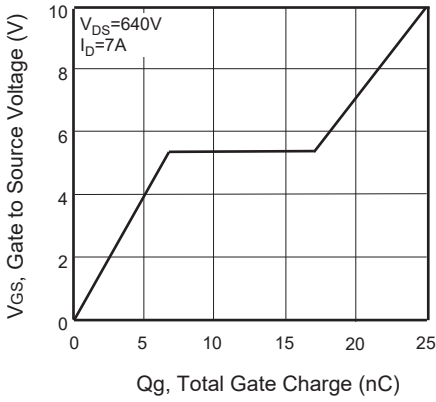
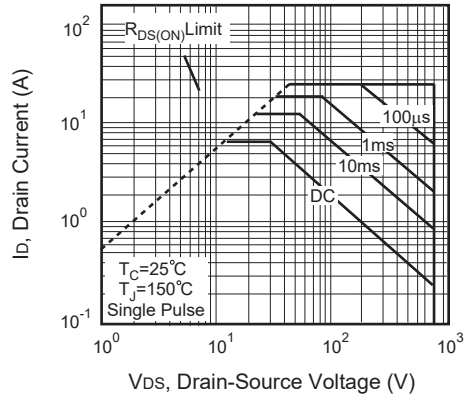


Figure 6. Body Diode Forward Voltage Variation with Source Current



**Figure 7. Gate Charge**



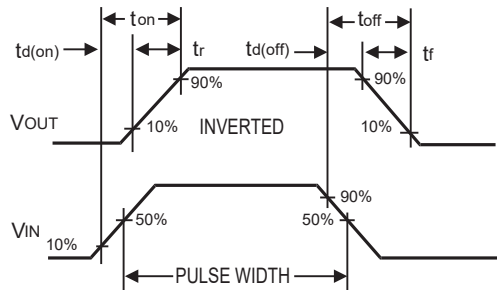
**Figure 8. Maximum Safe Operating Area**



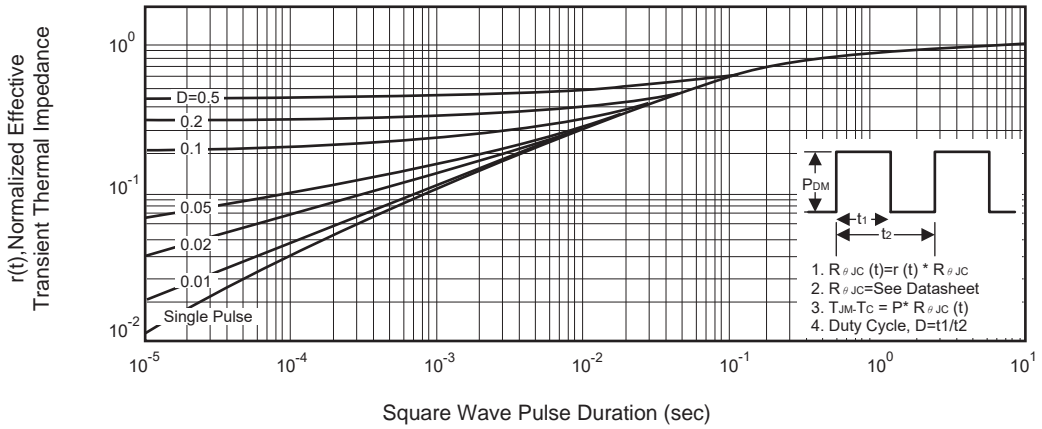
**Figure 9. Breakdown Voltage Variation VS Temperature**



**Figure 10. Switching Test Circuit**



**Figure 11. Switching Waveforms**



**Figure 12. Normalized Thermal Transient Impedance Curve**